DOCUMENT CHANGE REQUEST

DCR number 776

Changes required for: General

Originator: Steve Jeffery

Date: 2013/03/04

Date sent: 2013/02/06

Organisation: ESCC Executive

Status: IMPLEMENTED

Title:	Transistors High Power PNP, based on type 2N5153		
Number:	5204/002	Issue:	4

Other documents affected:

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Paragraph:

2.1.1

Original wording:

2.1.1 Deviations from the Generic Specification

2.1.1.1 Deviation from Screening Tests - Chart F3
High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.

2.1.1.2 Deviation from Qualification and Periodic Tests - Chart F4
For SMD.5, Terminal Strength is not applicable.

Proposed wording:

2.1.1 Deviations from the Generic Specification

2.1.1.1 Deviation from Qualification and Periodic Tests - Chart F4
For SMD.5, Terminal Strength is not applicable.

Justification:

With reference to DCR 275 (updating spec from Issue 2 to Issue 3), Para. 2.1.1.1 was added to this spec in error when the spec was converted to the new format. Para. 2.1.1.1 should be removed and Para. 2.1.1.2 re-numbered accordingly.

Attachments:
N/A
Modifications:
N/A
Approval signature:
Date signed:
2013-03-04